A universal nonvolatile processing environment

T. Windbacher, A. Makarov, V. Sverdlov, and S. Selberherr *Institute for Microelectronics, TU Wien, Vienna, Austria*

After decades of successful miniaturization, the soaring investment costs and the increasingly severe physical limits will bring CMOS scaling to a halt in the foreseeable future. Spintronics has attracted attention as a possible remedy, due to its non-volatility, high endurance, fast operation, and CMOS compatibility. New types of spintronic devices based on magnetic tunnel junctions (MTJs) utilizing all-electrical magnetization control, such as spin-torque (ST) transfer RAM and ST oscillators, have been successfully developed. However, even though promising spintronic solutions with respect to speed and power consumption have been already shown [1, 2], the employed MTJs are only used to store the information and, therefore, act as mere auxiliary devices, while the actual computation is still carried out via CMOS transistors. This leads to an increase in complexity and circuit footprint.

We propose a universal nonvolatile processing environment, consisting of an ST majority gate (STMG) [3] and a nonvolatile magnetic flip-flop [4], see Fig. 1(a). The flip-flops are adjacent to the STMGs in an array and act as shared local buffers. We discuss a possible realization of an easily extendible 1-bit full adder consisting of just a single STMG and three non-volatile flip-flops.

A further essential building block in modern electronics is the oscillator. Unfortunately, to date ST oscillators have required an external magnetic field, limiting their practical implementation. We have demonstrated that the nonvolatile magnetic flip-flop structure provides an ST oscillator [5], with an improved design shown in Fig. 1(b) [6]. This high-frequency oscillator needs no external magnetic field and complements perfectly the proposed nonvolatile processing environment. We discuss additional strategies to boost the maximum oscillator output power by using two three-layer in-plane MgO-MTJs.

The resulting nonvolatile processing environment features a highly regular structure, is computationally complete, and reduces the information transport due to its shared buffers. Thus, it is viable as a universal post CMOS logic technology.

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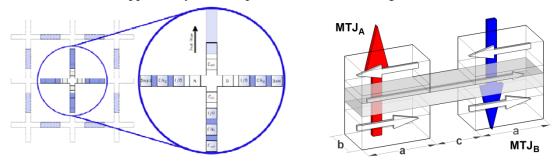


Fig. 1. (a) Spin torque majority gates (crosses) perform the computation, while the nonvolatile flip-flops (rectangles) act as shared buffers. A single STMG and three flip-flops are sufficient to realize a concatenated 1-bit full adder; (b) Schematic illustration of a spin-torque oscillator based on two MTJs. The colored arrows indicate the direction of the current for each of the MTJs.

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